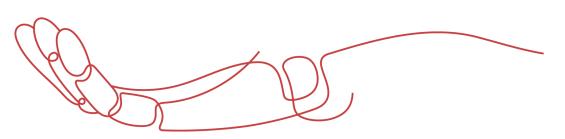


PRODUCT DATA SHEET



To learn more about JGSEMI, please visit our website at







Datasheet

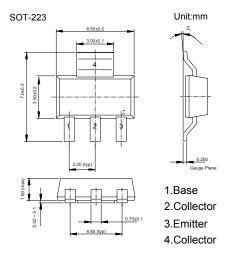
Samples

Please note: Please check the JINGAO Semiconductor website to verify the updated device numbers. The most current and up-to-date ordering information can be found at www.jg-semi.cn. Please email any questions regarding the system integration to JINGAO_questions@jgsemi.com.



Features

- High Voltage Driver Applications
- Complementary to PZTA42



Absolute Maximum Ratings Ta = 25℃

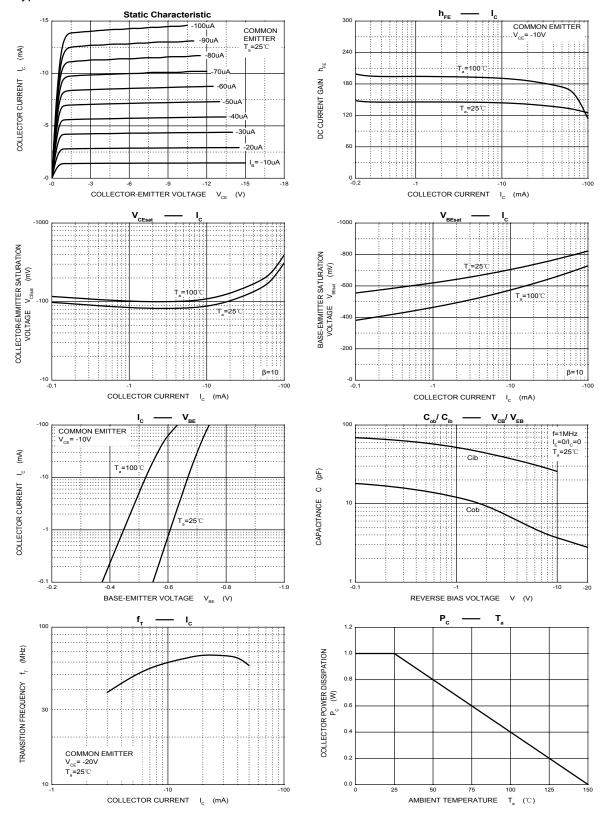
Parameter	Symbol	Rating	Unit	
Collector - Base Voltage	Vсво	-300	V	
Collector - Emitter Voltage	VCEO	-300		
Emitter - Base Voltage	VEBO	-5		
Collector Current - Continuous	Ic	-200	mA	
Collector Current - Pulse	ICP	-500		
Collector Power Dissipation	Pc	1	W	
Thermal Resistance from Junction to Ambient	Reja	125	°C/W	
Junction Temperature	TJ	150	$^{\circ}$	
Storage Temperature Range	Tstg	-55 to 150		

Electrical Characteristics Ta = 25℃

Parameter	Symbol	Test Conditions	Min	Тур	Max	Unit	
Collector- base breakdown voltage	Vсво	Ic= -100 μA, IE= 0	-300				
Collector- emitter breakdown voltage	VCEO	Ic= -1 mA, I _B = 0	-300			V	
Emitter - base breakdown voltage	VEBO	IE= -100 μ A, IC= 0	-5				
Collector-base cut-off current	Ісво	Vcb= -200 V , IE= 0			-250	nA	
Emitter cut-off current	ІЕВО	VEB= -4 V , IC=0			-100	IIA	
Collector-emitter saturation voltage	VCE(sat)	Ic=-20 mA, IB=-2mA			-0.5	V	
Base - emitter saturation voltage	VBE(sat)	Ic=-20 mA, IB=-2mA			-0.9	V	
DC current gain	hFE(1)	VcE= -10V, Ic=-1mA	25				
	hFE(2)	VcE= -10V, Ic= -10mA	40				
	hFE(3)	VcE= -10V, Ic=- 30mA	25				
Collector output capacitance	Cob	V _{CB} = -20V, I _E = 0,f=1MHz			6	pF	
Transition frequency	fτ	VcE= -20V, Ic= -10mA,f=100MHz	50			MHz	



Typical Characterisitics





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